

Description

The AST26CL is a Bi-directional TVS diode array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The AST26CL complies with the IEC 61000-4-2 (ESD) with $\pm 25\text{kV}$ air and $\pm 20\text{kV}$ contact discharge. It is assembled into a lead-free SOT-323 package. It is designed to protect components which are connected to data and transmission lines from voltage surges.

Features

- Protects two Bi-directional lines
- Ultra low leakage: nA level
- Operating voltage: 26V
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
Air discharge: $\pm 25\text{kV}$
Contact discharge: $\pm 20\text{kV}$
 - IEC61000-4-5 (Lightning) 3A (8/20 μs)
- RoHS Compliant

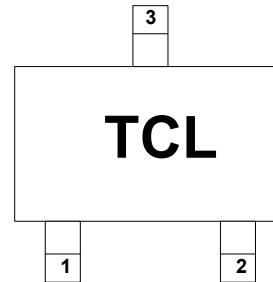
Mechanical Characteristics

- Package: SOT-323
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

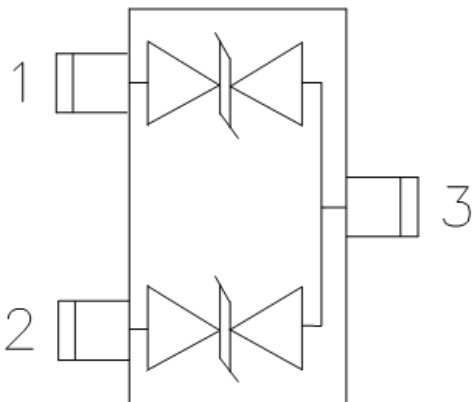
Applications

- Cellular Handsets and Accessories
- Notebooks and Handhelds
- Portable Instrumentation
- Set Top Box
- Industrial Controls
- Server and Desktop PC

Marking Information



Dimensions and Pin Configuration



Ordering Information

Part Number	Packaging	Reel Size
AST26CL	3000/Tape & Reel	7 inch

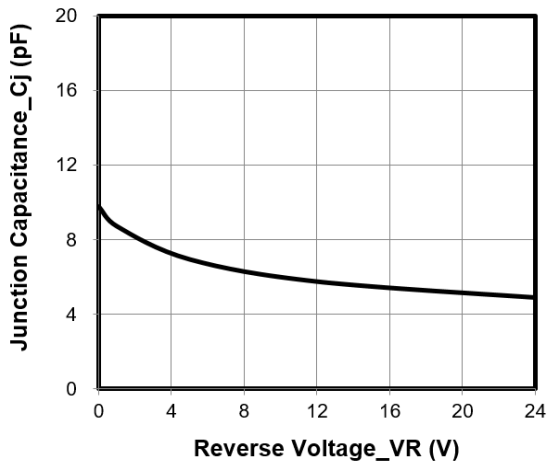
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	150	W
Peak Pulse Current (8/20 μs)	I _{PP}	3	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	± 25 ± 20	kV
Operating Temperature Range	T _J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^{\circ}\text{C}$

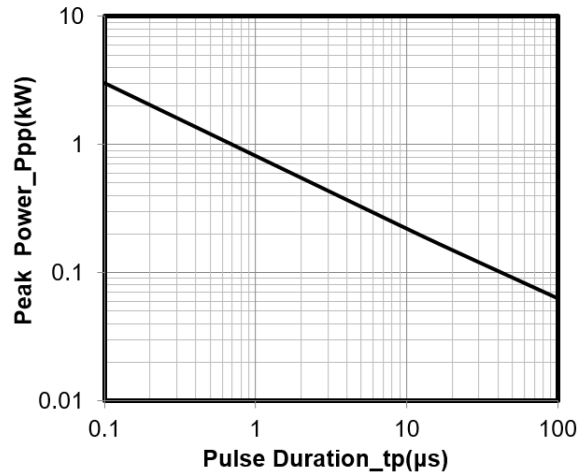
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			26	V	
Breakdown Voltage	V _{BR}	27			V	I _T = 1mA
Reverse Leakage Current	I _R			0.2	μA	V _{RWM} = 26V
Clamping Voltage	V _C			36	V	I _{PP} = 1A (8 x 20 μs pulse)
Clamping Voltage	V _C			50	V	I _{PP} = 3A (8 x 20 μs pulse)
Junction Capacitance	C _J		10		pF	V _R = 0V, f = 1MHz, Pin 1 to Pin 3 or Pin 2 to Pin 3
Junction Capacitance	C _J		5		pF	V _R = 0V, f = 1MHz, Pin 1 to Pin 2

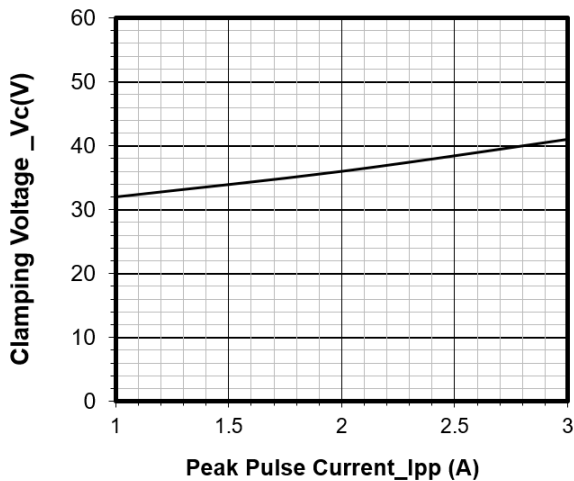
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



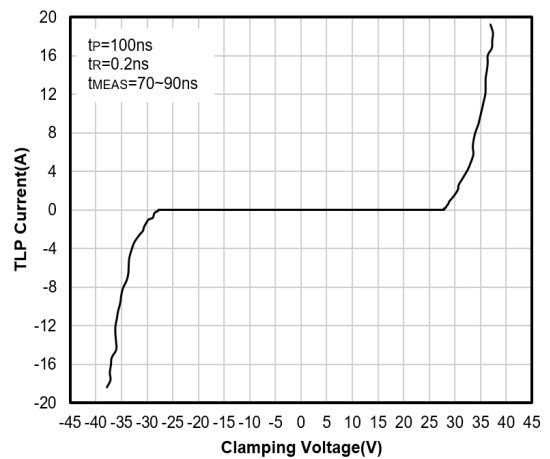
Junction Capacitance vs. Reverse Voltage



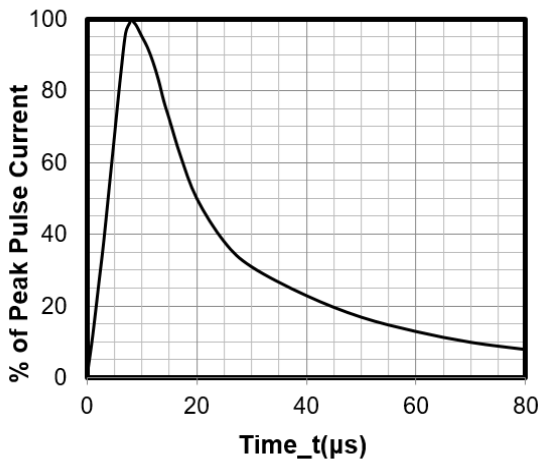
Peak Pulse Power vs. Pulse Time



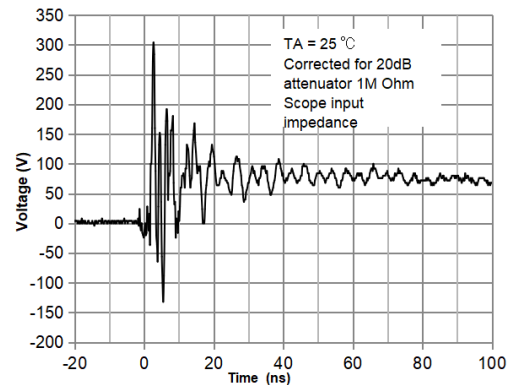
Clamping Voltage vs. Peak Pulse Current



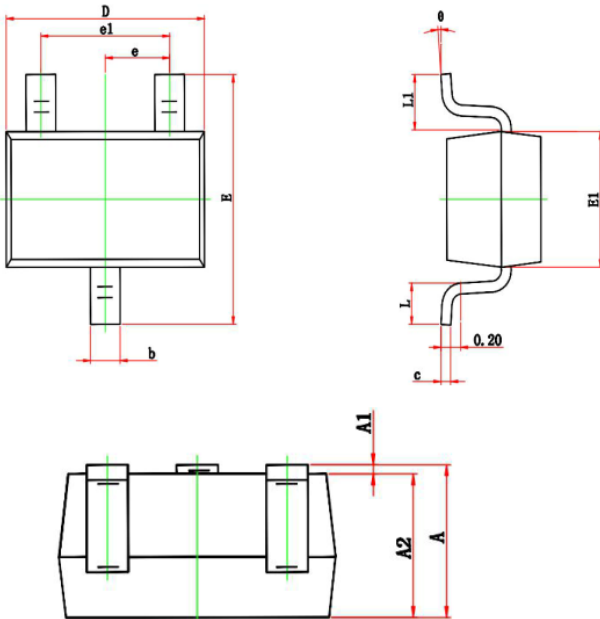
TLP Curve



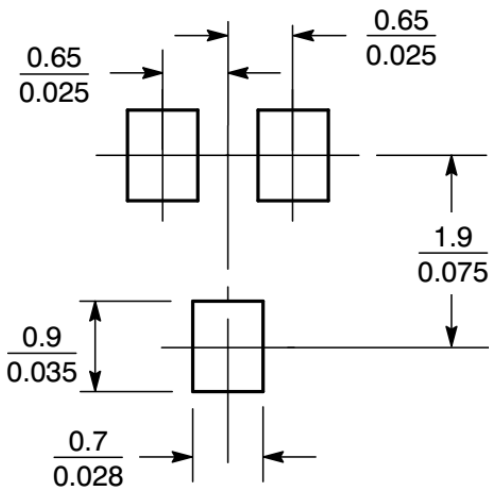
8 X 20μs Pulse Waveform



**Note: Data is taken with a 10x attenuator
ESD Clamping Voltage
8 kV Contact per IEC61000-4-2**

SOT-323 Package Outline Drawing


Symbol	Dim in mm		
	Min	Nor	Max
A	0.90	1.00	1.10
A1	0.00	0.05	0.10
A2	0.90	0.95	1.00
b	0.20	0.30	0.40
c	0.08	0.12	0.15
D	2.00	2.10	2.20
E	2.15	2.30	2.45
E1	1.15	1.25	1.35
e	0.650TPY.		
e1	1.2	1.3	1.4
L	0.26	0.36	0.46
L1	0.525REF.		
theta	0°	4°	8°

Suggested Land Pattern

Contact Information

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